

# RJK2055DPA

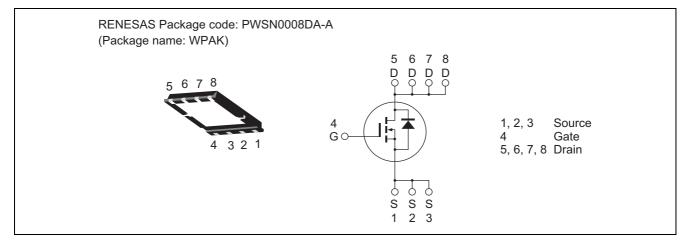
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1735-0100 Rev.1.00 Sep 16, 2008

# Features

- Low on-resistance
- Low drive current
- High density mounting

### Outline



# **Absolute Maximum Ratings**

ataSheet4U.com Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	200	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	Ι <sub>D</sub>	20	А
Drain peak current	Note1 D (pulse)	40	А
Body-drain diode reverse drain current	I <sub>DR</sub>	20	А
Body-drain diode reverse drain peak current	Note1 DR (pulse)	40	А
Avalanche current	I <sub>AP</sub> Note3	9	А
Avalanche energy	E <sub>AR</sub> <sup>Note3</sup>	5.4	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

2. Value at Tc = 25°C

3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

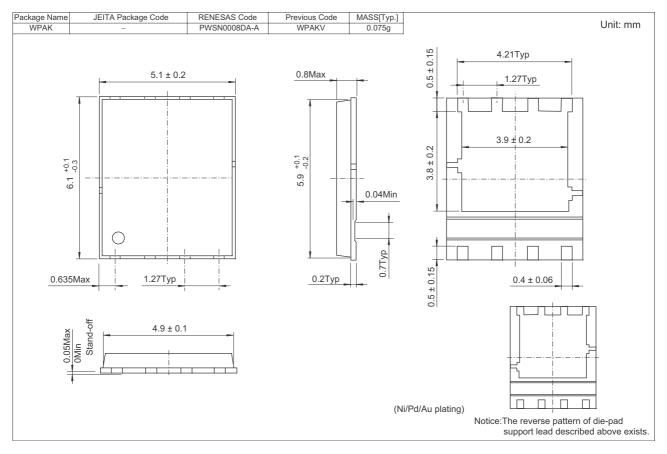
# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	200	_		V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 200 \text{ V}, \text{ V}_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±1	μΑ	$V_{GS} = \pm 30 \text{ V},  V_{DS} = 0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.5	_	4.5	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>		0.054	0.069	Ω	$I_D = 10 \text{ A}, \text{ V}_{GS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	2400	_	pF	$V_{DS} = 25 V$ $V_{GS} = 0$ f = 1 MHz
Output capacitance	Coss	_	245	_	pF	
Reverse transfer capacitance	Crss	_	55	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	37	_	ns	$I_D = 10 \text{ A}$ $V_{GS} = 10 \text{ V}$ $R_L = 10 \Omega$ $Rg = 10 \Omega$
Rise time	tr	_	17	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	_	64	—	ns	
Fall time	t <sub>f</sub>	—	17	—	ns	
Total gate charge	Qg	—	38	—	nC	V <sub>DD</sub> = 160 V
Gate to source charge	Qgs	_	11.5	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	—	9	—	nC	I <sub>D</sub> = 20 A
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.91	1.40	V	$I_F = 20 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	145	_	ns	$I_F = 20 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

Notes: 4. Pulse test

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# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK2055DPA-00-J0	2500 pcs	Taping

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